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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	468
Number of Logic Elements/Cells	3744
Total RAM Bits	18432
Number of I/O	189
Number of Gates	118000
Voltage - Supply	4.75V ~ 5.25V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	240-BFQFP Exposed Pad
Supplier Device Package	240-RQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epf10k70rc240-3

- Flexible interconnect
  - FastTrack® Interconnect continuous routing structure for fast, predictable interconnect delays
  - Dedicated carry chain that implements arithmetic functions such as fast adders, counters, and comparators (automatically used by software tools and megafunctions)
  - Dedicated cascade chain that implements high-speed, high-fan-in logic functions (automatically used by software tools and megafunctions)
  - Tri-state emulation that implements internal tri-state buses
  - Up to six global clock signals and four global clear signals
- Powerful I/O pins
  - Individual tri-state output enable control for each pin
  - Open-drain option on each I/O pin
  - Programmable output slew-rate control to reduce switching noise
  - FLEX 10KA devices support hot-socketing
- Peripheral register for fast setup and clock-to-output delay
- Flexible package options
  - Available in a variety of packages with 84 to 600 pins (see Tables 4 and 5)
  - Pin-compatibility with other FLEX 10K devices in the same package
  - FineLine BGA™ packages maximize board space efficiency
- Software design support and automatic place-and-route provided by Altera development systems for Windows-based PCs and Sun SPARCstation, HP 9000 Series 700/800 workstations
- Additional design entry and simulation support provided by EDIF 2 0 0 and 3 0 0 netlist files, library of parameterized modules (LPM), DesignWare components, Verilog HDL, VHDL, and other interfaces to popular EDA tools from manufacturers such as Cadence, Exemplar Logic, Mentor Graphics, OrCAD, Synopsys, Synplicity, VeriBest, and Viewlogic

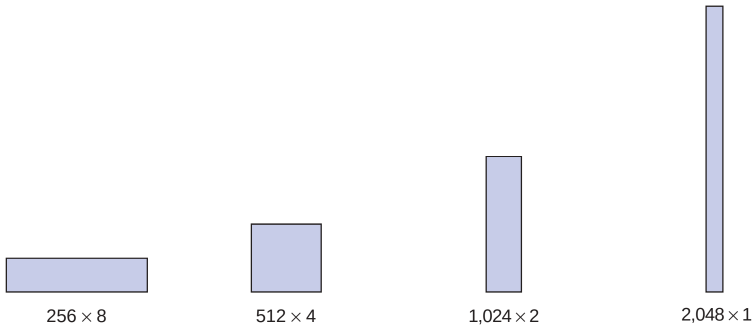
Logic functions are implemented by programming the EAB with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of EABs. The large capacity of EABs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or field-programmable gate array (FPGA) RAM blocks. For example, a single EAB can implement a 4 × 4 multiplier with eight inputs and eight outputs. Parameterized functions such as LPM functions can automatically take advantage of the EAB.

The EAB provides advantages over FPGAs, which implement on-board RAM as arrays of small, distributed RAM blocks. These FPGA RAM blocks contain delays that are less predictable as the size of the RAM increases. In addition, FPGA RAM blocks are prone to routing problems because small blocks of RAM must be connected together to make larger blocks. In contrast, EABs can be used to implement large, dedicated blocks of RAM that eliminate these timing and routing concerns.

EABs can be used to implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (`WE`) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the `WE` signal. In contrast, the EAB's synchronous RAM generates its own `WE` signal and is self-timed with respect to the global clock. A circuit using the EAB's self-timed RAM need only meet the setup and hold time specifications of the global clock.

When used as RAM, each EAB can be configured in any of the following sizes: 256 × 8, 512 × 4, 1,024 × 2, or 2,048 × 1. See Figure 2.

Figure 2. EAB Memory Configurations

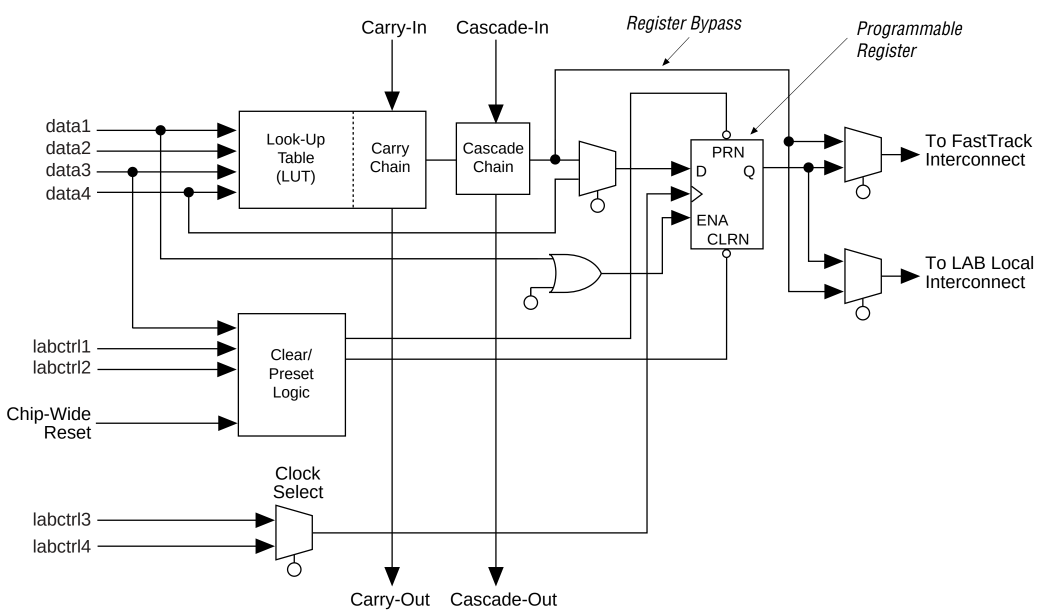


Each LAB provides four control signals with programmable inversion that can be used in all eight LEs. Two of these signals can be used as clocks; the other two can be used for clear/preset control. The LAB clocks can be driven by the dedicated clock input pins, global signals, I/O signals, or internal signals via the LAB local interconnect. The LAB preset and clear control signals can be driven by the global signals, I/O signals, or internal signals via the LAB local interconnect. The global control signals are typically used for global clock, clear, or preset signals because they provide asynchronous control with very low skew across the device. If logic is required on a control signal, it can be generated in one or more LEs in any LAB and driven into the local interconnect of the target LAB. In addition, the global control signals can be generated from LE outputs.

Logic Element

The LE, the smallest unit of logic in the FLEX 10K architecture, has a compact size that provides efficient logic utilization. Each LE contains a four-input LUT, which is a function generator that can quickly compute any function of four variables. In addition, each LE contains a programmable flipflop with a synchronous enable, a carry chain, and a cascade chain. Each LE drives both the local and the FastTrack Interconnect. See Figure 6.

Figure 6. FLEX 10K Logic Element



During compilation, the Compiler automatically selects the best control signal implementation. Because the clear and preset functions are active-low, the Compiler automatically assigns a logic high to an unused clear or preset.

The clear and preset logic is implemented in one of the following six modes chosen during design entry:

- Asynchronous clear
- Asynchronous preset
- Asynchronous clear and preset
- Asynchronous load with clear
- Asynchronous load with preset
- Asynchronous load without clear or preset

In addition to the six clear and preset modes, FLEX 10K devices provide a chip-wide reset pin that can reset all registers in the device. Use of this feature is set during design entry. In any of the clear and preset modes, the chip-wide reset overrides all other signals. Registers with asynchronous presets may be preset when the chip-wide reset is asserted. Inversion can be used to implement the asynchronous preset. Figure 10 shows examples of how to enter a section of a design for the desired functionality.

FastTrack Interconnect

In the FLEX 10K architecture, connections between LEs and device I/O pins are provided by the FastTrack Interconnect, which is a series of continuous horizontal and vertical routing channels that traverse the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack Interconnect consists of row and column interconnect channels that span the entire device. Each row of LABs is served by a dedicated row interconnect. The row interconnect can drive I/O pins and feed other LABs in the device. The column interconnect routes signals between rows and can drive I/O pins.

A row channel can be driven by an LE or by one of three column channels. These four signals feed dual 4-to-1 multiplexers that connect to two specific row channels. These multiplexers, which are connected to each LE, allow column channels to drive row channels even when all eight LEs in an LAB drive the row interconnect.

Each column of LABs is served by a dedicated column interconnect. The column interconnect can then drive I/O pins or another row's interconnect to route the signals to other LABs in the device. A signal from the column interconnect, which can be either the output of an LE or an input from an I/O pin, must be routed to the row interconnect before it can enter an LAB or EAB. Each row channel that is driven by an IOE or EAB can drive one specific column channel.

Access to row and column channels can be switched between LEs in adjacent pairs of LABs. For example, an LE in one LAB can drive the row and column channels normally driven by a particular LE in the adjacent LAB in the same row, and vice versa. This routing flexibility enables routing resources to be used more efficiently. See Figure 11.

Each IOE selects the clock, clear, clock enable, and output enable controls from a network of I/O control signals called the peripheral control bus. The peripheral control bus uses high-speed drivers to minimize signal skew across devices; it provides up to 12 peripheral control signals that can be allocated as follows:

- Up to eight output enable signals
- Up to six clock enable signals
- Up to two clock signals
- Up to two clear signals

If more than six clock enable or eight output enable signals are required, each IOE on the device can be controlled by clock enable and output enable signals driven by specific LEs. In addition to the two clock signals available on the peripheral control bus, each IOE can use one of two dedicated clock pins. Each peripheral control signal can be driven by any of the dedicated input pins or the first LE of each LAB in a particular row. In addition, an LE in a different row can drive a column interconnect, which causes a row interconnect to drive the peripheral control signal. The chip-wide reset signal will reset all IOE registers, overriding any other control signals.

Tables 8 and 9 list the sources for each peripheral control signal, and the rows that can drive global signals. These tables also show how the output enable, clock enable, clock, and clear signals share 12 peripheral control signals.

Signals on the peripheral control bus can also drive the four global signals, referred to as GLOBAL0 through GLOBAL3 in Tables 8 and 9. The internally generated signal can drive the global signal, providing the same low-skew, low-delay characteristics for an internally generated signal as for a signal driven by an input. This feature is ideal for internally generated clear or clock signals with high fan-out. When a global signal is driven by internal logic, the dedicated input pin that drives that global signal cannot be used. The dedicated input pin should be driven to a known logic state (such as ground) and not be allowed to float.

When the chip-wide output enable pin is held low, it will tri-state all pins on the device. This option can be set in the Global Project Device Options menu. Additionally, the registers in the IOE can be reset by holding the chip-wide reset pin low.

Row-to-IOE Connections

When an IOE is used as an input signal, it can drive two separate row channels. The signal is accessible by all LEs within that row. When an IOE is used as an output, the signal is driven by a multiplexer that selects a signal from the row channels. Up to eight IOEs connect to each side of each row channel. See Figure 14.

Figure 14. FLEX 10K Row-to-IOE Connections

The values for m and n are provided in Table 10.

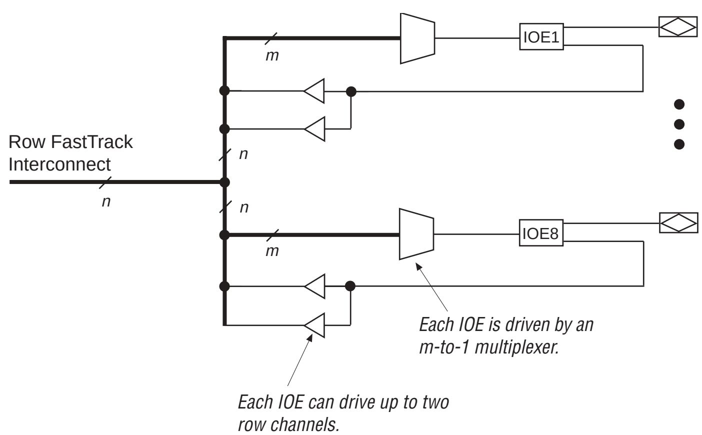


Figure 15. FLEX 10K Column-to-IOE Connections

The values for m and n are provided in Table 11.

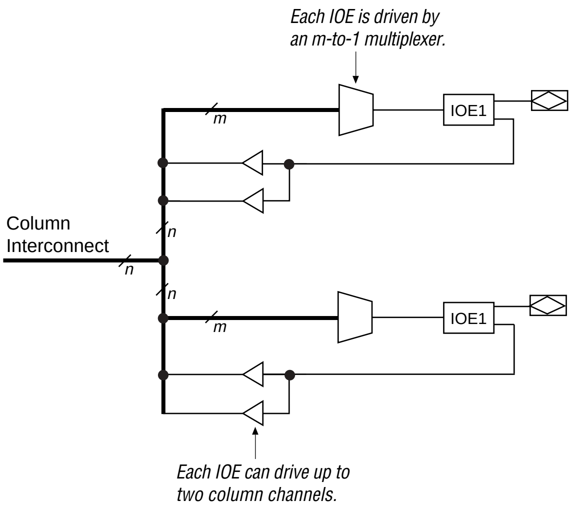


Table 11 lists the FLEX 10K column-to-IOE interconnect resources.

Table 11. FLEX 10K Column-to-IOE Interconnect Resources

Device	Channels per Column (*n*)	Column Channel per Pin (*m*)
EPF10K10 EPF10K10A	24	16
EPF10K20	24	16
EPF10K30 EPF10K30A	24	16
EPF10K40	24	16
EPF10K50 EPF10K50V	24	16
EPF10K70	24	16
EPF10K100 EPF10K100A	24	16
EPF10K130V	32	24
EPF10K250A	40	32

Table 13. FLEX 10K JTAG Instructions

JTAG Instruction	Description
SAMPLE/PRELOAD	Allows a snapshot of signals at the device pins to be captured and examined during normal device operation, and permits an initial data pattern output at the device pins.
EXTEST	Allows the external circuitry and board-level interconnections to be tested by forcing a test pattern at the output pins and capturing test results at the input pins.
BYPASS	Places the 1-bit bypass register between the `TDI` and `TDO` pins, which allows the BST data to pass synchronously through a selected device to adjacent devices during normal device operation.
USERCODE	Selects the user electronic signature (USERCODE) register and places it between the `TDI` and `TDO` pins, allowing the USERCODE to be serially shifted out of `TDO`.
IDCODE	Selects the IDCODE register and places it between `TDI` and `TDO`, allowing the IDCODE to be serially shifted out of `TDO`.
ICR Instructions	These instructions are used when configuring a FLEX 10K device via JTAG ports with a BitBlaster, or ByteBlasterMV or MasterBlaster download cable, or using a Jam File (**.jam**) or Jam Byte-Code File (**.jbc**) via an embedded processor.

The instruction register length of FLEX 10K devices is 10 bits. The USERCODE register length in FLEX 10K devices is 32 bits; 7 bits are determined by the user, and 25 bits are predetermined. Tables 14 and 15 show the boundary-scan register length and device IDCODE information for FLEX 10K devices.

Table 14. FLEX 10K Boundary-Scan Register Length

Device	Boundary-Scan Register Length
EPF10K10, EPF10K10A	480
EPF10K20	624
EPF10K30, EPF10K30A	768
EPF10K40	864
EPF10K50, EPF10K50V	960
EPF10K70	1,104
EPF10K100, EPF10K100A	1,248
EPF10K130V	1,440
EPF10K250A	1,440

Figure 22 shows the typical output drive characteristics of EPF10K10A, EPF10K30A, EPF10K100A, and EPF10K250A devices with 3.3-V and 2.5-V V_{CCIO}. The output driver is compliant with the 3.3-V ***PCI Local Bus Specification, Revision 2.2*** (with 3.3-V V_{CCIO}). Moreover, device analysis shows that the EPF10K10A, EPF10K30A, and EPF 10K100A devices can drive a 5.0-V PCI bus with eight or fewer loads.

Figure 22. Output Drive Characteristics for EPF10K10A, EPF10K30A & EPF10K100A Devices

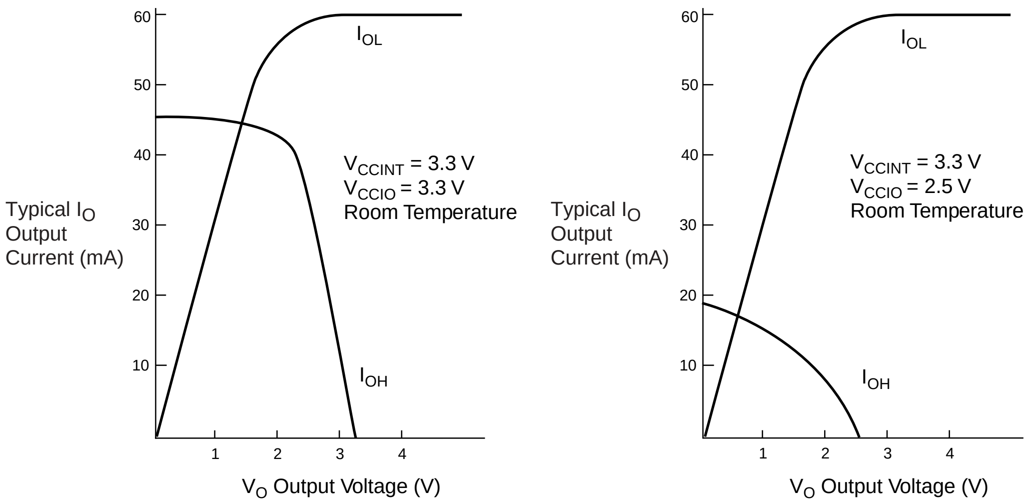
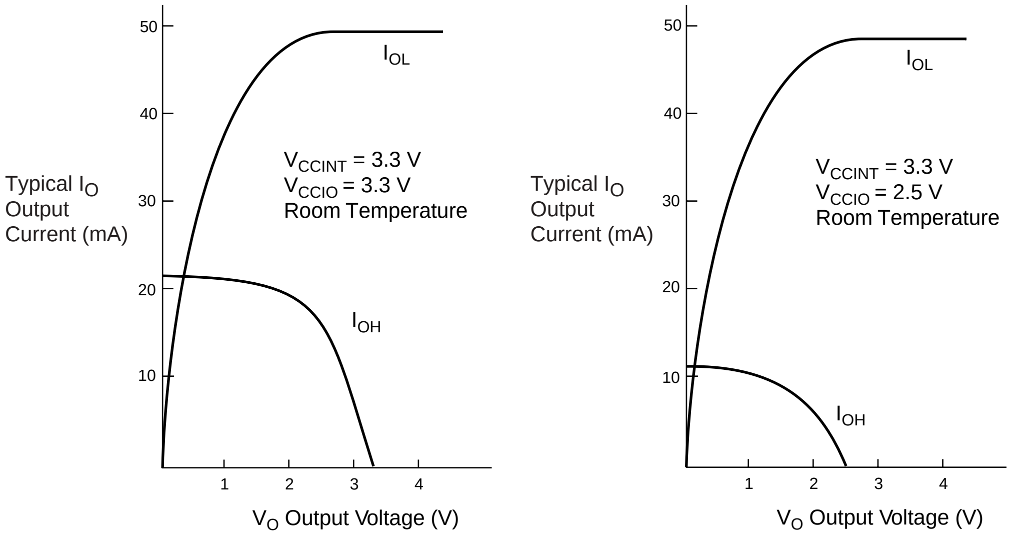


Figure 23 shows the typical output drive characteristics of the EPF10K250A device with 3.3-V and 2.5-V V_{CCIO}.

Figure 23. Output Drive Characteristics for EPF10K250A Device



Timing Model

The continuous, high-performance FastTrack Interconnect routing resources ensure predictable performance and accurate simulation and timing analysis. This predictable performance contrasts with that of FPGAs, which use a segmented connection scheme and therefore have unpredictable performance.

Device performance can be estimated by following the signal path from a source, through the interconnect, to the destination. For example, the registered performance between two LEs on the same row can be calculated by adding the following parameters:

- LE register clock-to-output delay (t_{CO})
- Interconnect delay ($t_{SAMEROW}$)
- LE look-up table delay (t_{LUT})
- LE register setup time (t_{SU})

The routing delay depends on the placement of the source and destination LEs. A more complex registered path may involve multiple combinatorial LEs between the source and destination LEs.

Figures 25 through 27 show the delays that correspond to various paths and functions within the LE, IOE, and EAB timing models.

Figure 25. FLEX 10K Device LE Timing Model

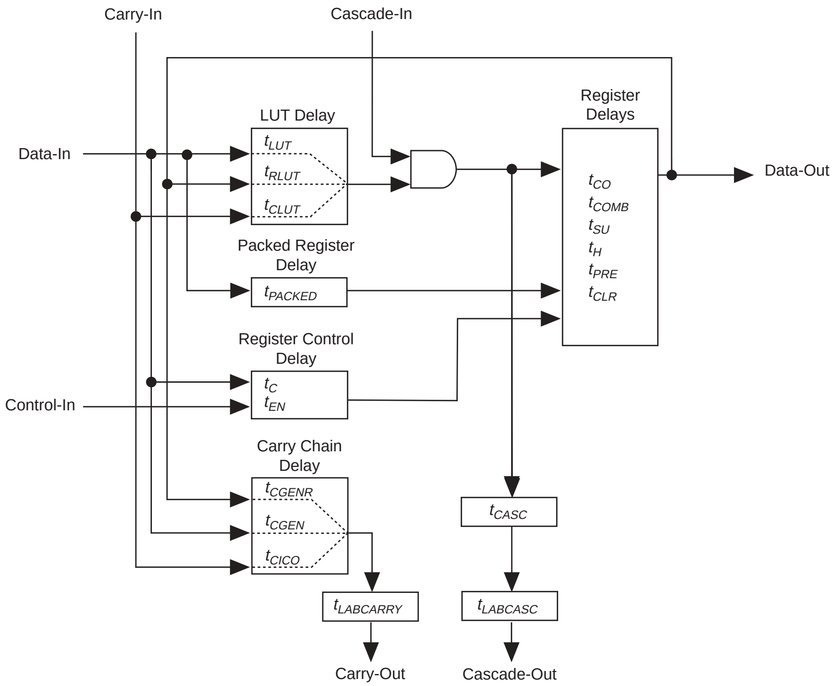
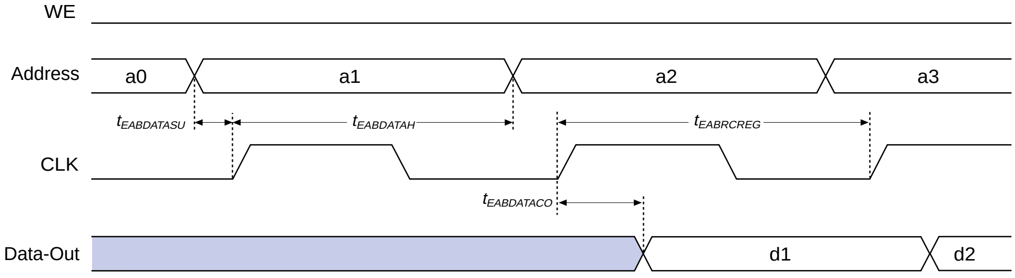


Table 35. EAB Timing Macroparameters *Notes (1), (6)*

Symbol	Parameter	Conditions
t_{EABAA}	EAB address access delay	
$t_{EABRCCOMB}$	EAB asynchronous read cycle time	
$t_{EABRCREG}$	EAB synchronous read cycle time	
t_{EABWP}	EAB write pulse width	
$t_{EABWCCOMB}$	EAB asynchronous write cycle time	
$t_{EABWCREG}$	EAB synchronous write cycle time	
t_{EABDD}	EAB data-in to data-out valid delay	
$t_{EABDATACO}$	EAB clock-to-output delay when using output registers	
$t_{EABDATASU}$	EAB data/address setup time before clock when using input register	
$t_{EABDATAH}$	EAB data/address hold time after clock when using input register	
$t_{EABWESU}$	EAB WE setup time before clock when using input register	
t_{EABWEH}	EAB WE hold time after clock when using input register	
$t_{EABWDSU}$	EAB data setup time before falling edge of write pulse when not using input registers	
t_{EABWDH}	EAB data hold time after falling edge of write pulse when not using input registers	
$t_{EABWASU}$	EAB address setup time before rising edge of write pulse when not using input registers	
t_{EABWAH}	EAB address hold time after falling edge of write pulse when not using input registers	
t_{EABWO}	EAB write enable to data output valid delay	

Figure 30. EAB Synchronous Timing Waveforms

EAB Synchronous Read



EAB Synchronous Write (EAB Output Registers Used)

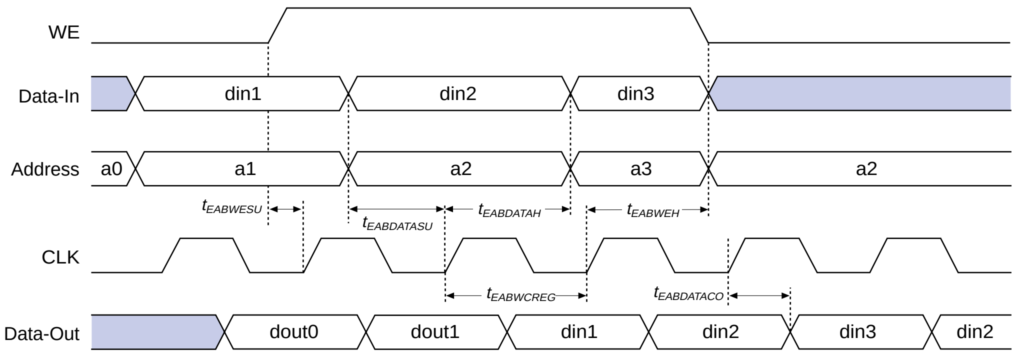


Table 51. EPF10K30, EPF10K40 & EPF10K50 Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	
t_{EABAA}		13.7		17.0	ns
$t_{EABRCCOMB}$	13.7		17.0		ns
$t_{EABRCREG}$	9.7		11.9		ns
t_{EABWP}	5.8		7.2		ns
$t_{EABWCCOMB}$	7.3		9.0		ns
$t_{EABWCREG}$	13.0		16.0		ns
t_{EABDD}		10.0		12.5	ns
$t_{EABDATACO}$		2.0		3.4	ns
$t_{EABDATASU}$	5.3		5.6		ns
$t_{EABDATAH}$	0.0		0.0		ns
$t_{EABWESU}$	5.5		5.8		ns
t_{EABWEH}	0.0		0.0		ns
$t_{EABWDSU}$	5.5		5.8		ns
t_{EABWDH}	0.0		0.0		ns
$t_{EABWASU}$	2.1		2.7		ns
t_{EABWAH}	0.0		0.0		ns
t_{EABWO}		9.5		11.8	ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 57 through 63 show EPF10K70 device internal and external timing parameters.

Table 57. EPF10K70 Device LE Timing Microparameters *Note (1)*

Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		1.3		1.5		2.0	ns
t_{CLUT}		0.4		0.4		0.5	ns
t_{RLUT}		1.5		1.6		2.0	ns
t_{PACKED}		0.8		0.9		1.3	ns
t_{EN}		0.8		0.9		1.2	ns
t_{CICO}		0.2		0.2		0.3	ns
t_{CGEN}		1.0		1.1		1.4	ns
t_{CGENR}		1.1		1.2		1.5	ns
t_{CASC}		1.0		1.1		1.3	ns
t_C		0.7		0.8		1.0	ns
t_{CO}		0.9		1.0		1.4	ns
t_{COMB}		0.4		0.5		0.7	ns
t_{SU}	1.9		2.1		2.6		ns
t_H	2.1		2.3		3.1		ns
t_{PRE}		0.9		1.0		1.4	ns
t_{CLR}		0.9		1.0		1.4	ns
t_{CH}	4.0		4.0		4.0		ns
t_{CL}	4.0		4.0		4.0		ns

Table 74. EPF10K50V Device EAB Internal Timing Macroparameters *Note (1)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{EABAA}		9.5		13.6		16.5		20.8	ns
$t_{EABRCCOMB}$	9.5		13.6		16.5		20.8		ns
$t_{EABRCREG}$	6.1		8.8		10.8		13.4		ns
t_{EABWP}	6.0		4.9		6.0		7.4		ns
$t_{EABWCCOMB}$	6.2		6.1		7.5		9.2		ns
$t_{EABWCREG}$	12.0		11.6		14.2		17.4		ns
t_{EABDD}		6.8		9.7		11.8		14.9	ns
$t_{EABDATACO}$		1.0		1.4		1.8		2.2	ns
$t_{EABDATASU}$	5.3		4.6		5.6		6.9		ns
$t_{EABDATAH}$	0.0		0.0		0.0		0.0		ns
$t_{EABWESU}$	4.4		4.8		5.8		7.2		ns
t_{EABWEH}	0.0		0.0		0.0		0.0		ns
$t_{EABWDSU}$	1.8		1.1		1.4		2.1		ns
t_{EABWDH}	0.0		0.0		0.0		0.0		ns
$t_{EABWASU}$	4.5		4.6		5.6		7.4		ns
t_{EABWAH}	0.0		0.0		0.0		0.0		ns
t_{EABWO}		5.1		9.4		11.4		14.0	ns

Table 80. EPF10K130V Device EAB Internal Microparameters *Note (1)*							
Symbol	-2 Speed Grade		-3 Speed Grade		-4 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
$t_{EABDATA1}$		1.9		2.4		2.4	ns
$t_{EABDATA2}$		3.7		4.7		4.7	ns
t_{EABWE1}		1.9		2.4		2.4	ns
t_{EABWE2}		3.7		4.7		4.7	ns
t_{EABCLK}		0.7		0.9		0.9	ns
t_{EABCO}		0.5		0.6		0.6	ns
$t_{EABBYPASS}$		0.6		0.8		0.8	ns
t_{EABSU}	1.4		1.8		1.8		ns
t_{EABH}	0.0		0.0		0.0		ns
t_{AA}		5.6		7.1		7.1	ns
t_{WP}	3.7		4.7		4.7		ns
t_{WDSU}	4.6		5.9		5.9		ns
t_{WDH}	0.0		0.0		0.0		ns
t_{WASU}	3.9		5.0		5.0		ns
t_{WAH}	0.0		0.0		0.0		ns
t_{WO}		5.6		7.1		7.1	ns
t_{DD}		5.6		7.1		7.1	ns
t_{EABOUT}		2.4		3.1		3.1	ns
t_{EABCH}	4.0		4.0		4.0		ns
t_{EABCL}	4.0		4.7		4.7		ns

Notes to tables:
(1) All timing parameters are described in Tables 32 through 38 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

Tables 92 through 98 show EPF10K30A device internal and external timing parameters.

Table 92. EPF10K30A Device LE Timing Microparameters Note (1)

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{LUT}		0.8		1.1		1.5	ns
t_{CLUT}		0.6		0.7		1.0	ns
t_{RLUT}		1.2		1.5		2.0	ns
t_{PACKED}		0.6		0.6		1.0	ns
t_{EN}		1.3		1.5		2.0	ns
t_{CICO}		0.2		0.3		0.4	ns
t_{CGEN}		0.8		1.0		1.3	ns
t_{CGENR}		0.6		0.8		1.0	ns
t_{CASC}		0.9		1.1		1.4	ns
t_C		1.1		1.3		1.7	ns
t_{CO}		0.4		0.6		0.7	ns
t_{COMB}		0.6		0.7		0.9	ns
t_{SU}	0.9		0.9		1.4		ns
t_H	1.1		1.3		1.7		ns
t_{PRE}		0.5		0.6		0.8	ns
t_{CLR}		0.5		0.6		0.8	ns
t_{CH}	3.0		3.5		4.0		ns
t_{CL}	3.0		3.5		4.0		ns

Table 93. EPF10K30A Device IOE Timing Microparameters Note (1) *(Part 1 of 2)*

Symbol	-1 Speed Grade		-2 Speed Grade		-3 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	
t_{IOD}		2.2		2.6		3.4	ns
t_{IOC}		0.3		0.3		0.5	ns
t_{IOCO}		0.2		0.2		0.3	ns
t_{IOCOMB}		0.5		0.6		0.8	ns
t_{IOSU}	1.4		1.7		2.2		ns

Notes to tables:

(1) All timing parameters are described in Tables 32 through 37 in this data sheet.
(2) Using an LE to register the signal may provide a lower setup time.
(3) This parameter is specified by characterization.

ClockLock & ClockBoost Timing Parameters

For the ClockLock and ClockBoost circuitry to function properly, the incoming clock must meet certain requirements. If these specifications are not met, the circuitry may not lock onto the incoming clock, which generates an erroneous clock within the device. The clock generated by the ClockLock and ClockBoost circuitry must also meet certain specifications. If the incoming clock meets these requirements during configuration, the ClockLock and ClockBoost circuitry will lock onto the clock during configuration. The circuit will be ready for use immediately after configuration. Figure 31 illustrates the incoming and generated clock specifications.

Figure 31. Specifications for the Incoming & Generated Clocks

The t_I parameter refers to the nominal input clock period; the t_O parameter refers to the nominal output clock period.

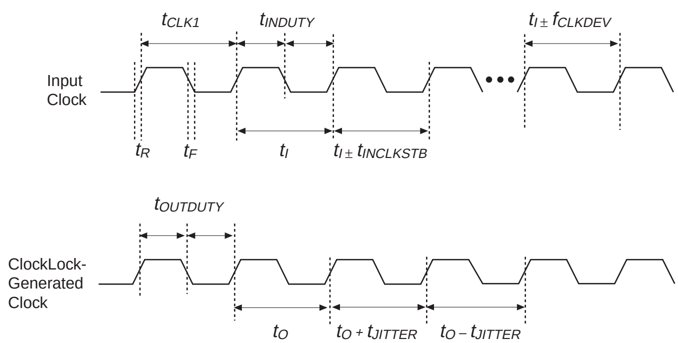


Table 113 summarizes the ClockLock and ClockBoost parameters.

Table 113. ClockLock & ClockBoost Parameters (Part 1 of 2)

Symbol	Parameter	Min	Typ	Max	Unit
t_R	Input rise time			2	ns
t_F	Input fall time			2	ns
t_{INDUTY}	Input duty cycle	45		55	%
f_{CLK1}	Input clock frequency (ClockBoost clock multiplication factor equals 1)	30		80	MHz
t_{CLK1}	Input clock period (ClockBoost clock multiplication factor equals 1)	12.5		33.3	ns
f_{CLK2}	Input clock frequency (ClockBoost clock multiplication factor equals 2)	16		50	MHz
t_{CLK2}	Input clock period (ClockBoost clock multiplication factor equals 2)	20		62.5	ns